

Yong-Hee Lee

List of Publications by Year in descending order

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11
papers

627
citations

2258059

3
h-index

1372567

10
g-index

12
all docs

12
docs citations

12
times ranked

938
citing authors

#	ARTICLE	IF	CITATIONS
1	Comprehensive defect suppression in perovskite nanocrystals for high-efficiency light-emitting diodes. <i>Nature Photonics</i> , 2021, 15, 148-155.	31.4	590
2	Adhesion Performance and UV-Curing Behaviors of Interpenetrated Structured Pressure Sensitive Adhesives with 3-MPTS for Si-Wafer Dicing Process. <i>Journal of Adhesion Science and Technology</i> , 2012, 26, 1629-1643.	2.6	15
3	Synthesis and properties of flexible polyester with urethane polyol for automotive pre-coated metals. <i>Journal of Adhesion Science and Technology</i> , 2016, 30, 1537-1554.	2.6	8
4	Progress of p-channel bottom-gate poly-Si thin-film transistor by nickel silicide seed-induced lateral crystallization. <i>Applied Physics A: Materials Science and Processing</i> , 2016, 122, 1.	2.3	3
5	Bottom-gate poly-Si thin-film transistors by nickel silicide seed-induced lateral crystallization with self-aligned lightly doped layer. <i>Solid-State Electronics</i> , 2017, 129, 6-9.	1.4	3
6	Advanced Four-Mask Process Bottom-Gate Poly-Si TFT via Self-Aligned NiSi ₂ Seed-Induced Lateral Crystallization. <i>IEEE Electron Device Letters</i> , 2016, 37, 1292-1294.	3.9	2
7	Effect of Ultrathin Silicon Oxide Film for Enhanced Performance and Reliability of Metal-Induced Laterally Crystallized Thin-Film Transistors Using Silicon Nitride as a Gate Dielectric. <i>ECS Journal of Solid State Science and Technology</i> , 2016, 5, Q279-Q283.	1.8	2
8	Annealing effect of sputter-grown Pt/Ni ₈₀ Fe ₂₀ /Pt sandwich trilayer films on Gilbert damping. <i>Journal of Applied Physics</i> , 2020, 128, 223901.	2.5	2
9	Electrical Properties of Bottom Gate Poly-Si TFTs by NiSi ₂ Seed-Induced Lateral Crystallization and Its Applications. <i>MRS Advances</i> , 2016, 1, 3429-3433.	0.9	1
10	Novel Fabrication of Lightly Doped-Drain for Suppressing the Leakage Current in Polycrystalline Silicon Thin-Film Transistor. <i>Journal of Nanoscience and Nanotechnology</i> , 2017, 17, 3465-3468.	0.9	1
11	Direct/Indirect Junction Between Channel Inversion Layer and Doped Source/Drain Region on Metal-Induced Lateral Crystallization Polycrystalline Silicon Bottom Gate TFTs. <i>IEEE Transactions on Electron Devices</i> , 2017, 64, 432-437.	3.0	0